

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

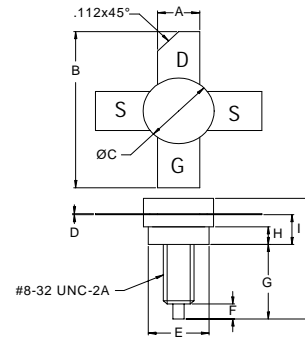
The **ASI TVV010** is Designed for Television Band III Applications up to 225 MHz.

FEATURES:

- Common Emitter
- $P_G = 10$ dB at 10 W/225 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	2.2°C/W

PACKAGE STYLE .380 4L STUD


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10656
CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CER}	$I_C = 50$ mA $R_{BE} = 10 \Omega$	60			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_E = 28$ V			5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
P_{GE}	$V_{CE} = 25$ V $I_C = 1.6$ A $f = 225$ MHz	10			dB
IMD_1	$P_{OUT} = 10$ W	-54			dBc